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(54) Title: DIRECT ATOMIC LAYER DEPOSITION AND/OR ETCHING METHOD

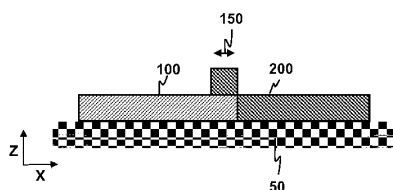


FIG 1A

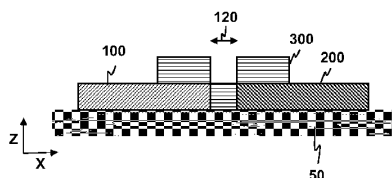


FIG 1B

(57) Abstract: The disclosure relates an atomic layer deposition and/or etching method comprising drawing, using a first precursor fluid, on a substrate a first line extending longitudinally and having, in lateral direction, a first linewidth, and drawing, using a second precursor fluid, on the substrate a second line extending longitudinally and having, in lateral direction, a second linewidth. The first and second lines partly overlap one another laterally by less than the first linewidth and the second linewidth, and/or the first and second lines are laterally spaced apart from one another by less than the first linewidth and the second linewidth, such that a first protrusion is formed of which a largest width in lateral direction is smaller than the first linewidth and the second linewidth, and/or a first recess is formed of which a largest width, in lateral direction, is smaller than the first linewidth and the second linewidth.

SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,  
GQ, GW, KM, ML, MR, NE, SN, TD, TG).

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